

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**PRELIMINARY AMENDMENT ACCOMPANYING APPLICATION**

APPLICANT: Etsuo Morita

ATTY. DOCKET NO. 09792909-4715

SERIAL NO.

DATE FILED:

INVENTION: "METHOD OF MANUFACTURING CRYSTAL OF III-V  
COMPOUND OF THE NITRIDE SYSTEM, CRYSTAL  
SUBSTRATE OF III-V COMPOUND OF THE NITRIDE SYSTEM,  
CRYSTAL FILM OF III-V COMPOUND OF THE NITRIDE  
SYSTEM, AND METHOD OF MANUFACTURING DEVICE"

Assistant Commissioner of Patents  
Washington, D.C. 20231

S I R:

Between the title and the heading "Background of the Invention" on page 1, insert the following:

--RELATED APPLICATION DATA

The present application claims priority to Japanese Application No. P11-345246 filed December 3, 1999, which application is incorporated herein by reference to the extent permitted by law.

Respectfully submitted,



(Reg. No. 32,919)

David R. Metzger  
SONNENSCHN NATH & ROSENTHAL  
P.O. Box #061080  
Wacker Drive Station  
Sears Tower  
Chicago, IL 60606-1080  
Customer #26263

Attorneys for Applicant(s)

09726860-13000